

Silicon PNP Power Transistors

2SB812

DESCRIPTION

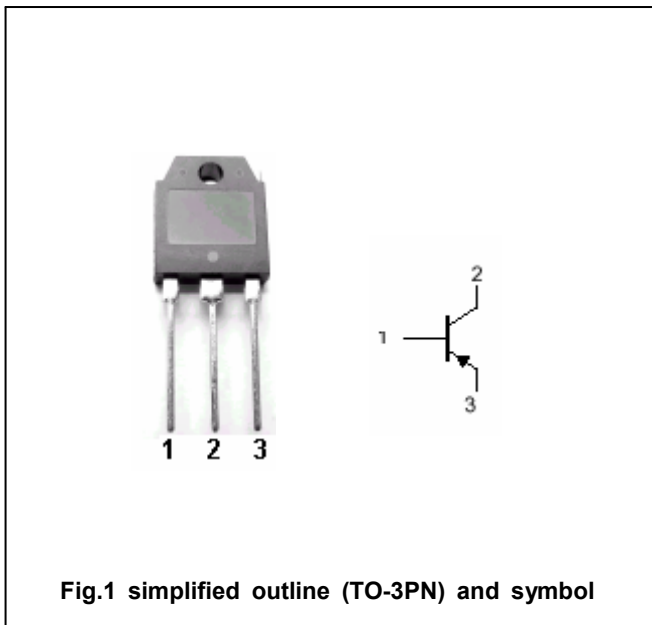
- With TO-3PN package
- Wide area of safe operation
- Low collector saturation voltage

APPLICATIONS

- For audio frequency output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current (DC)		-4	A
P _C	Collector power dissipation	T _C =25°C	60	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-40~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ;I _B =0	-60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ;I _E =0	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ;I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A ;I _B =-0.3A			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-1A;V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-4V	40		250	

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PACKAGE OUTLINE

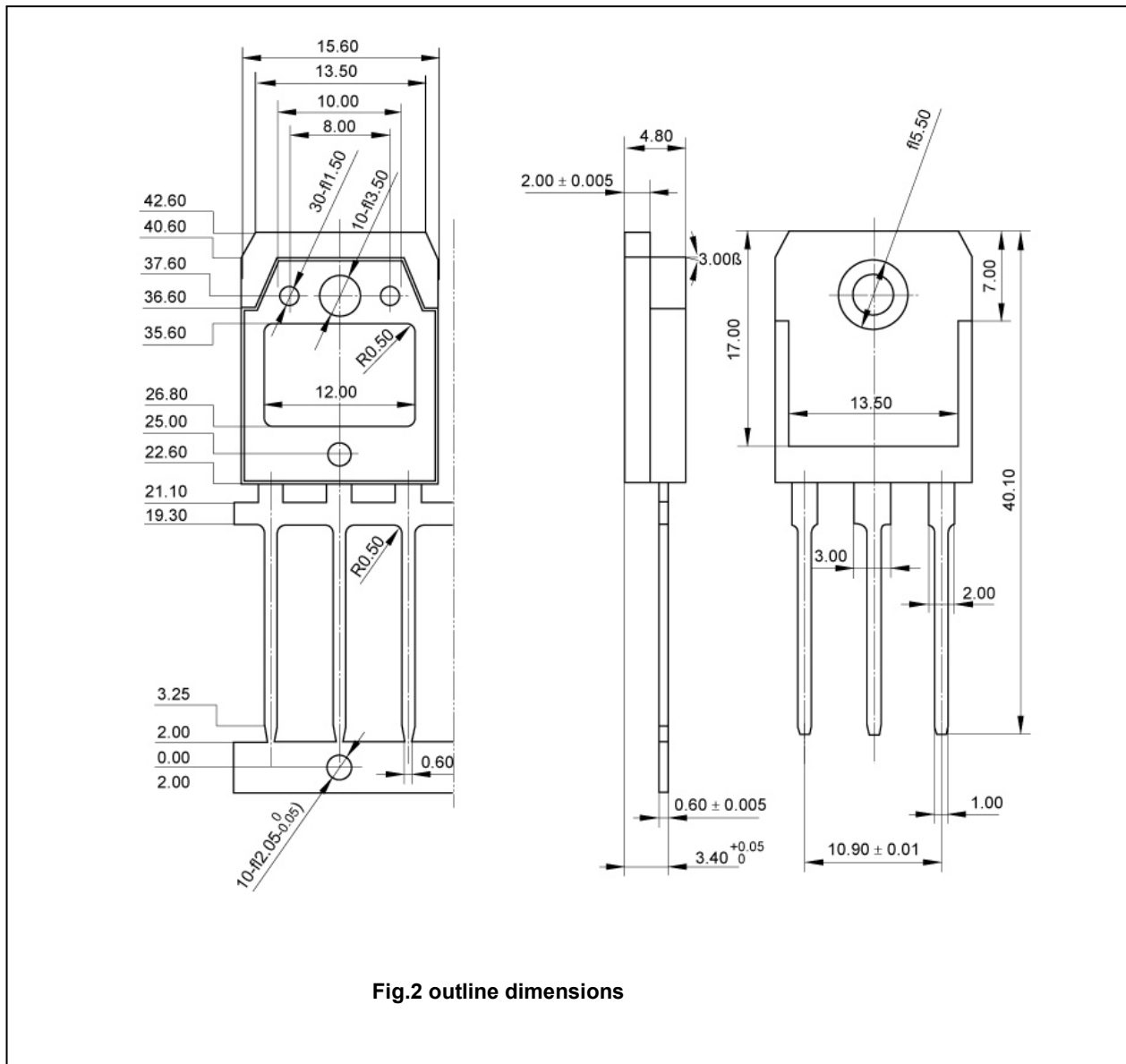


Fig.2 outline dimensions